

ABSTRACT OF THE DISCLOSURE

A semiconductor laser device according to the present invention comprises a laminated structure of a semiconductor material including an active layer formed of a quantum well structure, a low-reflection film formed on one end face of the structure, and a high-reflection film formed on the other end face of the structure. The cavity length (L) of the device is $1,200 \mu\text{m}$ or more. This laser device, which enjoys high kink currents and a satisfactorily linear current-optical output characteristic, is a useful pumping light source for optical fiber amplifier.